

Silicon NPN Power Transistors

2SC1448

DESCRIPTION

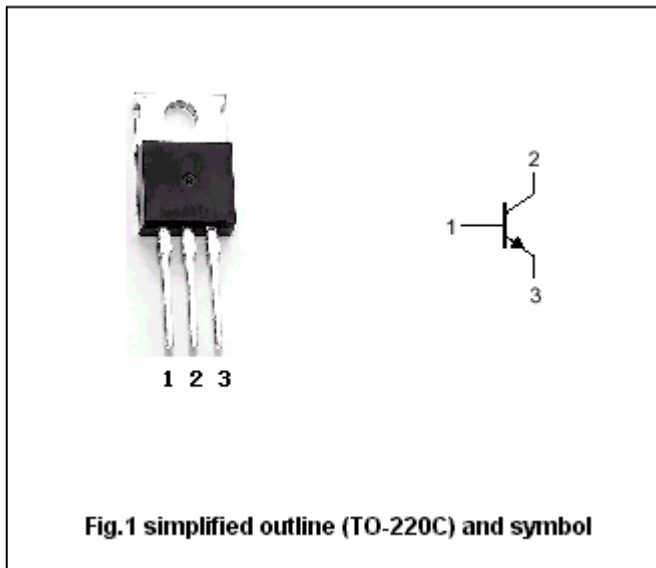
- With TO-220 package
- High collector-emitter breakdown voltage  
:  $V_{CEO}=150V(\text{min})$

APPLICATIONS

- Power amplifier applications
- Vertical output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings ( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	150	V
$V_{CEO}$	Collector-emitter voltage	Open base	150	V
$V_{EBO}$	Emitter-base voltage	Open collector	5	V
$I_C$	Collector current		1.5	A
$I_B$	Base current		0.5	A
$P_C$	Collector power dissipation	$T_a=25^\circ\text{C}$	1.5	W
		$T_C=25^\circ\text{C}$	25	
$T_j$	Junction temperature		150	$^\circ\text{C}$
$T_{stg}$	Storage temperature		-55~150	$^\circ\text{C}$

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## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =30mA; I <sub>B</sub> =0	150			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =1mA; I <sub>C</sub> =0	5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =0.5A; I <sub>B</sub> =50m A			1.5	V
I <sub>CB0</sub>	Collector cut-off current	V <sub>CB</sub> =150V; I <sub>E</sub> =0			20	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			20	μA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =0.5A ; V <sub>CE</sub> =10V	40		140	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.5A ; V <sub>CE</sub> =10V		5		MHz

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PACKAGE OUTLINE

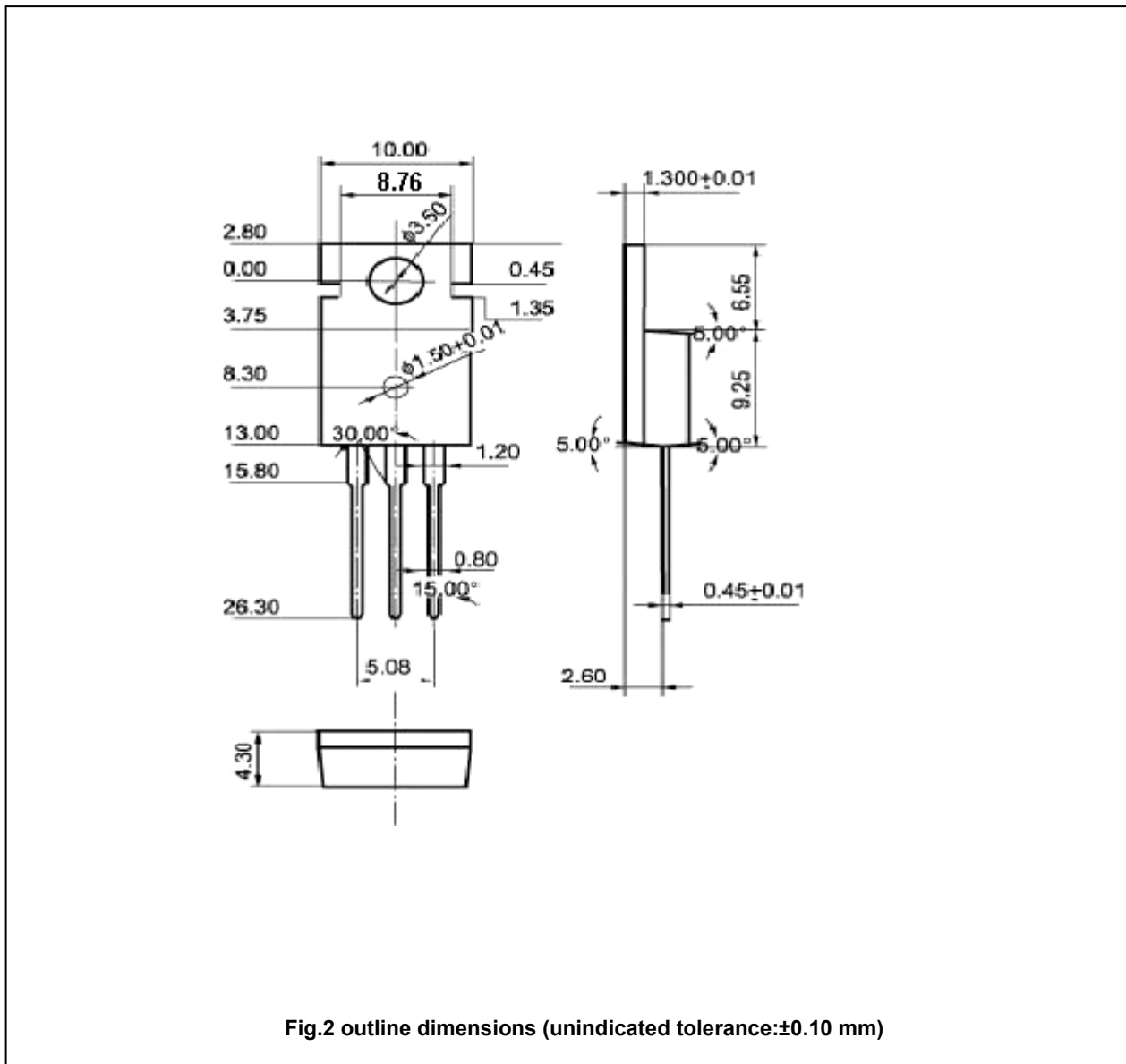


Fig.2 outline dimensions (unindicated tolerance:±0.10 mm)